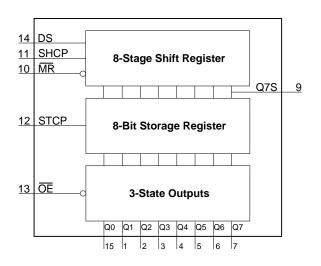


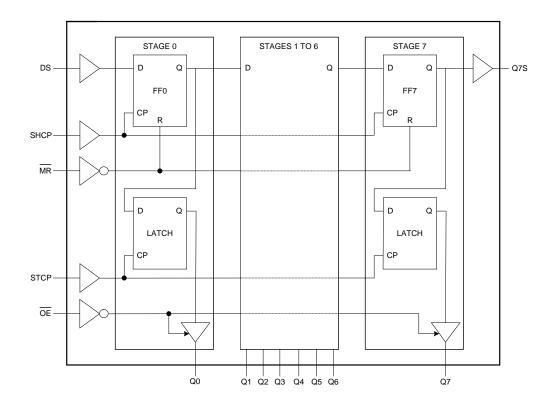
# Pin Descriptions

Pin Number	Pin Name	Function
1	Q1	Parallel Data Output 1
2	Q2	Parallel Data Output 2
3	Q3	Parallel Data Output 3
4	Q4	Parallel Data Output 4
5	Q5	Parallel Data Output 5
6	Q6	Parallel Data Output 6
7	Q7	Parallel Data Output 7
8	GND	Ground
9	Q7S	Serial Data Output
10	MR	Master Reset Input
11	SHCP	Shift Register Clock Input
12	STCP	Storage Register Clock Input
13	ŌĒ	Output Enable Input
14	DS	Serial Data Input
15	Q0	Parallel Data Output 0
16	Vcc	Supply Voltage

# **Functional Diagram**



# **Logic Diagram**

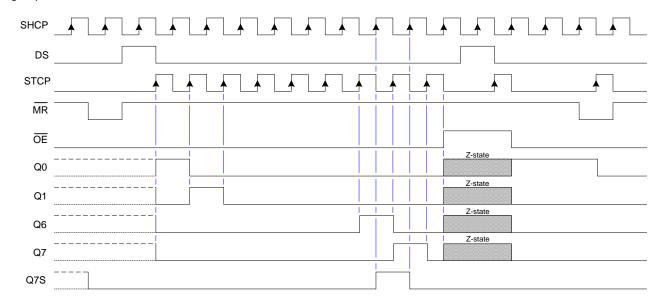




## **Functional Description and Timing Diagram**

	Control			Input	Output		Familia
SHCP	STCP	OE	MR	DS	Q7S	Qn	Function
Х	Х	L	L	-	L NC		Low-level asserted on MR clears shift register. Storage register is unchanged.
Х	1	L	L	-	L L		Empty shift register transferred to storage register.
Х	X	Н	L	-	L	Z	Shift register remains clear; All Q ouputs in Z state.
<b>↑</b>	Х	L	Н	-	Q6S NC HIGH is shifted into first stage of Shift Register Contents register shifted to next register.  The content of Q6S has been shifted to Q7S and now appropriate to Q7S and now appropriate to Q7S.		HIGH is shifted into first stage of Shift Register Contents of each register shifted to next register.  The content of Q6S has been shifted to Q7S and now appears on device pin Q7S.
Х	<b>↑</b>	L	Н	-	NC	Contents of shift register copied to storage register. With	
<b>↑</b>	<b>↑</b>	L	Н	-	Q6S	QnS	Contents of shift register copied to output register then shift register shifted.

H=HIGH Voltage State L=LOW Voltage State ↑=LOW to HIGH Transition X= Don'T Care – High or Low (Not Floating) NC= No Change Z= High-Impedance State





#### Absolute Maximum Ratings (Note 4) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Des	Rating	Unit		
ESD HBM	Human Body Model ESD Protection	2	kV		
ESD CDM	Charged Device Model ESD Prote	ction	1	kV	
ESD MM	Machine Model ESD Protection		200	V	
Vcc	Supply Voltage Range		-0.5 to +7.0	V	
VI	Input Voltage Range		-0.5 to +7.0	V	
Vo	Voltage Applied to Output in High	or Low State	-0.3 to V <sub>CC</sub> +0.5	V	
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < -0.5V		-20	mA	
lıĸ	Input Clamp Current V <sub>I</sub> > V <sub>CC</sub> +	Input Clamp Current V <sub>I</sub> > V <sub>CC</sub> +0.5V			
lok	Output Clamp Current Vo < -0.5	V	-20	mA	
I <sub>OK</sub>	Output Clamp Current V <sub>O</sub> > V <sub>CC</sub>	+0.5V	20	mA	
		Q7 Standard Output	±25	mA	
lo	Continuous Output Current	Qn Bus Driver Outputs	±35	mA	
Icc	Continuous Current through Vdd o	r GND	70	mA	
I <sub>GND</sub>	Continuous Current through Vdd o	r GND	-70	mA	
TJ	Operating Junction Temperature		-40 to +150	°C	
T <sub>STG</sub>	Storage Temperature		-65 to +150	°C	
P <sub>TOT</sub>	Total Power Dissipation		500	mW	

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

## Recommended Operating Conditions (Note 5) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Max	Unit
Vcc	Supply Voltage	_	2.0	6.0	V
VI	Input Voltage	_	0	Vcc	V
Vo	Output Voltage	Active Mode	0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.0V	-	1000	ns/V
Δt/ΔV	Input Transition Rise or Fall Rate	V <sub>CC</sub> = 4.5V	ı	500	115/ V
		V <sub>CC</sub> = 6.0V	-	400	-
T <sub>A</sub>	Operating Free-Air Temperature	_	-40	+125	°C

Note: 5. Unused inputs should be held at  $V_{CC}$  or Ground.



#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

0		To al Com ditions	v	T	A = +25°(	<b>:</b>	T <sub>A</sub> = -40°C	to +85°C	T <sub>A</sub> = -40°C	to +125°C	
Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
		_	2.0V	1.5	1.2	_	1.5	_	1.5	_	
V <sub>IH</sub>	High-Level Input Voltage	_	4.5V	3.15	2.4	_	3.15	_	3.15	-	V
	Input voltage	_	6.0V	4.2	3.2	_	4.2	_	4.2	_	
		_	2.0V	_	0.8	0.5	-	0.5	-	0.5	
$V_{IL}$	Low-Level Input Voltage	_	4.5V	_	2.1	1.35	-	1.35	_	1.35	V
	input voitage	_	6.0V	_	2.8	1.8	-	1.8	-	1.8	
	High-Level		2.0V	1.9	2.0	-	1.9	_	1.9	=	
	Output	I <sub>OH</sub> = -20μA	4.5V	4.4	4.5	_	4.4	_	4.4	-	
	Voltage	All Outputs	6.0V	5.9	6.0	_	5.9	-	5.9	_	
Vон	0=0.0	I <sub>OH</sub> = -4.0mA	4.5V	3.84	4.32	_	4.32	-	3.7	_	V
	Q7S Output	I <sub>OH</sub> = -5.2mA	6.0V	5.34	5.81	-	5.81	_	5.2	_	
	Qn Bus	I <sub>OH</sub> = -6.0mA	4.5V	3.84	4.32	-	4.32	_	3.7	_	
	Outputs	I <sub>OH</sub> = -7.8mA	6.0V	5.34	5.81	-	5.81	_	5.2	_	
	Low-Level		2.0V	_	0	0.1	-	0.1	_	0.1	
	Output Voltage	I <sub>OL</sub> = 20µA	4.5V	_	0	0.1	-	0.1	_	0.1	
		All Outputs	6.0V	_	0	0.1	-	0.1	_	0.1	
VoL	070.0	I <sub>OL</sub> = 4.0mA	4.5V	_	.15	0.33	-	0.33	_	0.4	V
	Q7S Output	I <sub>OL</sub> = 5.2mA	6.0V	_	.16	0.33	-	0.33	_	0.4	
	Qn Bus	$I_{OL} = 6.0 \text{mA}$	4.5V	_	.15	0.33	-	0.33	_	0.4	
	Outputs	I <sub>OL</sub> = 7.8mA	6.0V	_	.16	0.33	-	0.33	_	0.4	
I <sub>I</sub>	Input Current	V <sub>I</sub> =GND to 5.5V	6.0V	_	-	±0.1	-	± 1	_	± 1	μA
loz	OFF-State Output Current	Qn Internal High or Low Vo = V <sub>CC</sub> or GND	6.0V	-	-	± 5	-	± 5	-	± 10	μА
I <sub>CC</sub>	Supply Current	$V_I = GND \text{ or } V_{CC}$ $I_O = 0$	6.0V	-	-	8.0	-	80	-	160	μА
C <sub>i</sub>	Input Capacitance	$V_1 = V_{CC}$ or GND	6.0V	_	4	10	_	10	_	10	pF

# Operating Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter		Test Conditions	V <sub>CC</sub> = 5V Typ	Unit
C <sub>pd</sub> Power Dissipation Capacitance f = 1 MHz All Outputs Switching-No Load		f = 1 MHz All Outputs Switching-No Load	43	pF

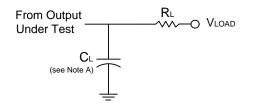


# **Switching Characteristics**

Symbol /	Dia a	Took Conditions	V	-	T <sub>A</sub> = +25°(	С	-40°C to	o +85°C	-40°C to	+125°C	l lm!4						
Parameter	Pins	Test Conditions	V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit						
f <sub>MAX</sub>			2.0V	9	30	_	4.8	_	4	-							
Maximum	SHCP or STCP	Figure 1	4.5V	30	91	_	24	_	20	_	MHz						
Frequency	3105		6.0V	35	108	_	28	_	24	_							
	SHCP		2.0V	75	17	_	95	_	110	_							
	SHCP HIGH or	Figure 1	4.5V	15	6	=	19	-	22	-							
	LOW		6.0V	13	5	=	16	_	19	-							
	STCP		2.0V	75	11	_	95	_	110	_							
t <sub>W</sub> Pulse Width	HIGH or	Figure 1	4.5V	15	4	_	19	_	22	_	ns						
Puise Width	LOW		6.0V	13	3	_	16	_	19	_							
			2.0V	75	17	_	95	_	110	-							
	MR LOW	Figure 1	4.5V	15	6	_	19	_	22	_							
			6.0V	13	5	_	16	_	19	_							
	DO .		2.0V	50	11	_	65	_	75	_							
	DS to SHCP	Figure 1	4.5V	10	4	_	13	_	15	_	ns						
tsu	01101		6.0V	9	3	_	11	_	13	-							
Set-up Time	01105	SHCP tp STCP Figure 1	2.0V	75	22	_	95	_	110	-							
			4.5V	15	8	_	19	_	22	_	ns						
			6.0V	13	7	_	16	_	19	_							
	DC +-		2.0V	3	-6	-	3	-	3	-	ns						
t <sub>H</sub> Hold Time	DS to SHCP		4.5V	3	-2	_	3	_	3	_							
rioid riirie	01101		6.0V	3	-2	_	3	_	3	_							
									2.0V	50	-19	-	65	_	75	_	
t <sub>REC</sub> Recovery Time	MR to SHCP	Figure 1	4.5V	10	-7	-	13	_	15	_	ns						
Recovery Time	31101		6.0V	9	-6	-	11	_	13	_							
	OLIOD (-	Figure 1	2.0V	-	52	160	-	200	-	240							
	SHCP to Q7S	C <sub>L</sub> =50pF	4.5V	=	19	32	-	40	=	48	ns						
t <sub>PD</sub>	α, σ	OL=30PI	6.0V	=	15	27	-	34	=	41							
Propagation Delay	CTCD to	Figure 1	2.0V	=	55	175	-	220	=	265							
_ 5.5.	STCP to Qn	C <sub>L</sub> =50pF	4.5V	=	20	35	-	44	=	53	ns						
	ζ	OL=30pi	6.0V	=	16	30	-	37	=	45							
t <sub>PHL</sub>		Figure 1	2.0V	-	47	175	-	220	-	265							
Propagation	MR to Q7S	C <sub>L</sub> =50pF	4.5V	-	17	35	-	44	-	53	ns						
Delay		OL=00P1	6.0V	-	14	30	_	37	-	45							
<b>-</b>		Figure 1	2.0V	=	47	150	-	190	-	225							
t <sub>EN</sub> Enable Time	OE to Qn	C <sub>L</sub> =50pF	4.5V	=	17	30	-	38	-	45	ns						
LIADIC IIIIG		0 <u>L</u> =30pi	6.0V	=	14	26	=	33	=	38	1						
		Figure 1	2.0V	=	41	150	-	190	-	225							
t <sub>DIS</sub> Disable Time	OE to Qn	C <sub>L</sub> =50pF	4.5V	=	15	30	=	38	-	45	ns						
DISGDIC TITLE		OL-20bi	6.0V	=	12	26	-	33	-	38							

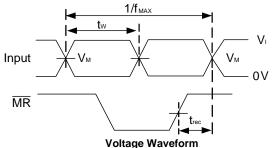


#### **Parameter Measurement Information**

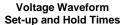


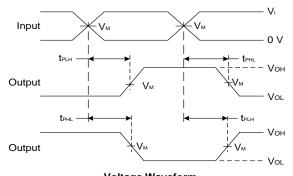
TEST	$V_{LOAD}$
tplh/tphl	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vcc
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

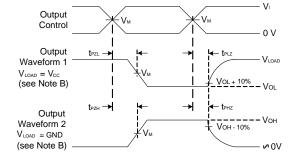
V <sub>CC</sub>		Inputs	V <sub>M</sub>	C <sub>L</sub>
	VI	t <sub>r</sub> /t <sub>f</sub>		1
2.0V	Vcc	6ns	V <sub>CC</sub> /2	50pF
4.5V	Vcc	6ns	V <sub>CC</sub> /2	50pF
6.0V	V <sub>CC</sub>	6ns	V <sub>CC</sub> /2	50pF



Voltage Waveform Pulse Duration and Recovery Time







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Voltage Waveform Enable and Disable Times

Notes: A. Includes test lead and test apparatus capacitance.

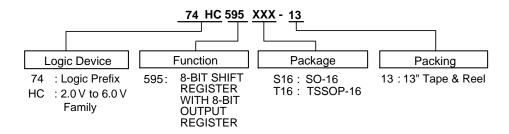
- B. Output Waveform 1 depends on the internal Q<sub>N</sub> node being low and behaves in this manner based on OE pin.

  Output Waveform 2 depends on the internal Q<sub>N</sub> node being high and behaves in this manner based on OE pin.
- C. All pulses are supplied at pulse repetition rate ≤ 10MHz.
- D. Inputs are measured separately one transition per measurement.
- E. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD.</sub>

Figure 1. Load Circuit and Voltage Waveforms



## **Ordering Information**

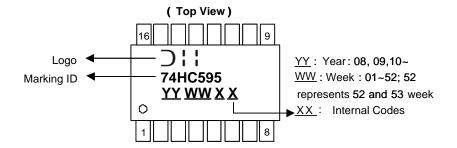


Part Number	Package Code Packaging		7" Tape and Reel (Note 6)		
Part Number	Package Code	Fackaging	Quantity	Part Number Suffix	
74HC595S16-13	S16	SO-16	2500/Tape & Reel	-13	
74HC595T16-13	T16	TSSOP-16	2500/Tape & Reel	-13	

Note: 6. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

#### (1) SO-16, TSSOP16



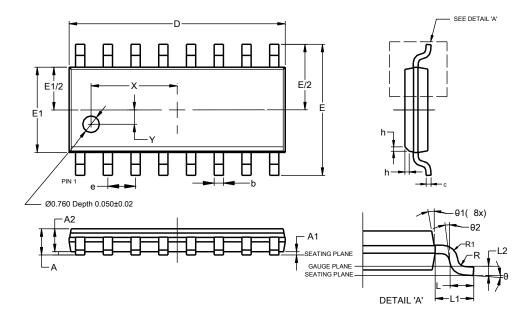
Part Number	Package
74HC595S16	SO-16
74HC595T16	TSSOP-16



#### Package Outline Dimensions (All dimensions in mm.)

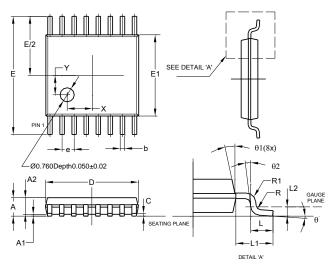
Please see http://www.diodes.com/package-outlines.html for the latest version.

#### Package Type: SO-16



SO-16							
Dim	Min	Max	Тур				
Α		1.260					
<b>A</b> 1	0.10	0.23					
A2	1.02						
b	0.31	0.51					
C	0.10	0.25					
D	9.80	10.00					
Е	5.90	6.10					
E1	3.80	4.00					
е	1	.27 BS	C				
h	0.15	0.25	0.20				
L	0.40	1.27					
L1	1	.04 RE	F				
L2	C	).25 BS(	)				
R	0.07						
R1	0.07						
Χ		945 RE					
Υ		.661 RE	F				
θ	0° 8°						
θ1	5° 15°						
θ2	0°						
All	Dimens	ions in	mm				

#### Package Type: TSSOP-16



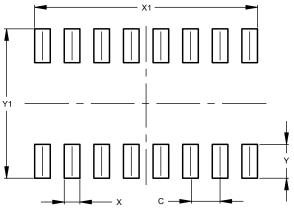
TSSOP-16			
Dim	Min	Max	Тур
Α	-	1.08	-
A1	0.05	0.15	-
A2	0.80	0.93	-
b	0.19	0.30	-
С	0.09	0.20	-
D	4.90	5.10	-
Е	6.40 BSC		
E1	4.30	4.50	-
е	0.65 BSC		
L	0.45	0.75	-
L1	1.00 REF		
L2	0.25 BSC		
R / R1	0.09	-	-
Х	-	-	1.350
Y	-	-	1.050
θ	0°	8°	-
θ1	5°	15°	-
θ2	0°	-	-
All Dimensions in mm			



#### **Suggested Pad Layout**

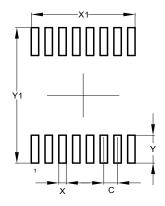
Please see http://www.diodes.com/package-outlines.html for the latest version.

Package Type: SO-16



Dimensions	Value (in mm)
С	1.270
Х	0.670
X1	9.560
Y	1.450
Y1	6.400

Package Type: TSSOP-16



Dimensions	Value (in mm)
С	0.650
Х	0.350
X1	4.900
Υ	1.400
Y1	6.800



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